

# BCR12FM-14LC

700V - 12A - Triac

Medium Power Use

R07DS1411EJ0101

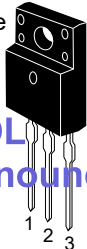
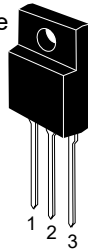
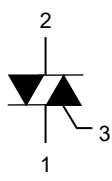
Rev.1.01

Feb. 19, 2019

## Features

- $I_T (RMS)$  : 12 A
- $V_{DRM}$  : 800 V ( $T_j=125^\circ\text{C}$ )
- $T_j$ : 150°C
- $I_{FGT1}$ ,  $I_{RGT1}$ ,  $I_{RGT III}$ : 50 mA
- Insulated Type
- Planar Passivation Type
- Viso: 2000 V

## Outline

<p>RENESAS Package code: PRSS0003AG-A (Package name: TO-220FP) Ordering code #BB0</p>  <p><b>EOL announced</b></p>	<p>RENESAS Package code: PRSS0003AP-A (Package name: TO-220FPA) Ordering code #BG0</p> 	 <p>1. T<sub>1</sub> Terminal 2. T<sub>2</sub> Terminal 3. Gate Terminal</p>
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## Application

Low inrush current AC load.

## Maximum Ratings

Parameter	Symbol	Voltage class	Unit	Conditions
		14		
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	800	V	$T_j=125^\circ\text{C}$
		700	V	$T_j=150^\circ\text{C}$
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	800	V	

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_T (RMS)$	12	A	Commercial frequency, sine full wave 360°conduction, $T_c = 77^\circ\text{C}$
Surge on-state current	$I_{TSM}$	72	A	60 Hz sinewave 1 full cycle, peak value, non-repetitive
$I^2t$ for fusion	$I^2t$	21.6	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60 Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	5	W	
Average gate power dissipation	$P_{G (AV)}$	0.5	W	
Peak gate voltage	$V_{GM}$	10	V	
Peak gate current	$I_{GM}$	2	A	
Junction Temperature	$T_j$	-40 to +150	°C	
Storage temperature	$T_{stg}$	-40 to +150	°C	
Isolation voltage <sup>Note6</sup>	$V_{iso}$	2000	V	$T_a=25^\circ\text{C}$ , AC 1 minute, T <sub>1</sub> • T <sub>2</sub> • G terminal to case

Notes: 1. Gate open.

## Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current	$I_{DRM}$	—	—	2.0	mA	$T_j = 150^\circ\text{C}$ , $V_{DRM}$ applied
On-state voltage	$V_{TM}$	—	—	1.75	V	$T_c = 25^\circ\text{C}$ , $I_{TM} = 20\text{ A}$ , instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGTI}$	—	—	1.5	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{ V}$ , $R_L = 6\ \Omega$ , $R_G = 330\ \Omega$
	II	$V_{RGTI}$	—	—	1.5	
	III	$V_{RGTIII}$	—	—	1.5	
Gate trigger current <sup>Note2</sup>	I	$I_{FGTI}$	—	—	50	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{ V}$ , $R_L = 6\ \Omega$ , $R_G = 330\ \Omega$
	II	$I_{RGTI}$	—	—	50	
	III	$I_{RGTIII}$	—	—	50	
Gate non-trigger voltage	$V_{GD}$	0.2	—	—	V	$T_j = 125^\circ\text{C}$ , $V_D = 1/2 V_{DRM}$
Thermal resistance	$R_{th(j-c)}$	—	—	4.3	$^\circ\text{C/W}$	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutation voltage <sup>Note4</sup>	$(dv/dt)_c$	10	—	—	$\text{V}/\mu\text{s}$	$T_j = 125^\circ\text{C}$

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance  $R_{th(c-f)}$  in case of greasing is  $0.5^\circ\text{C/W}$ .

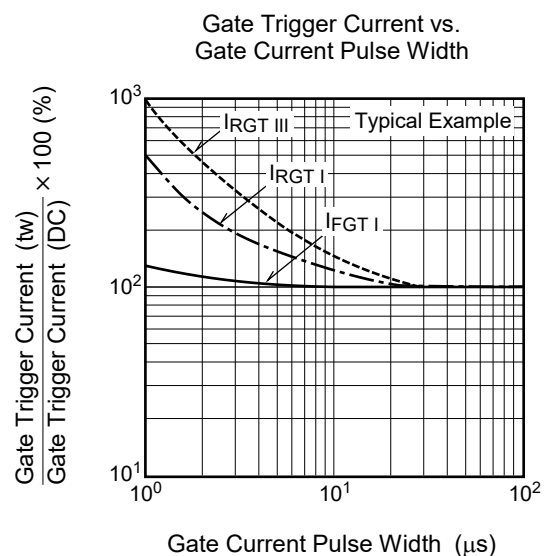
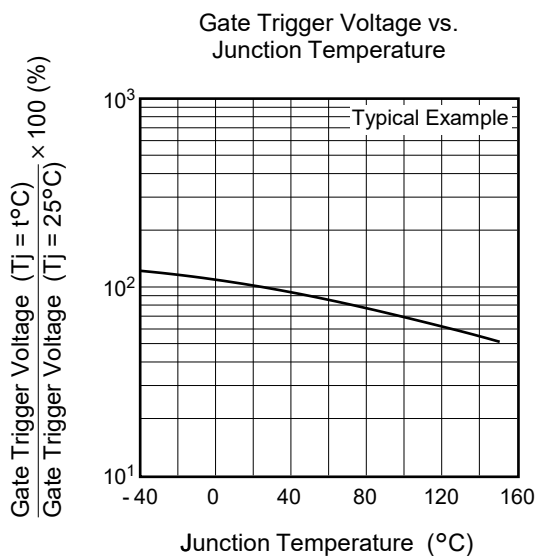
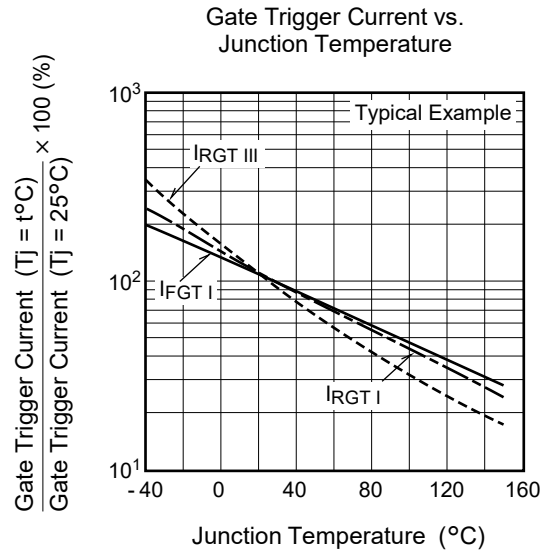
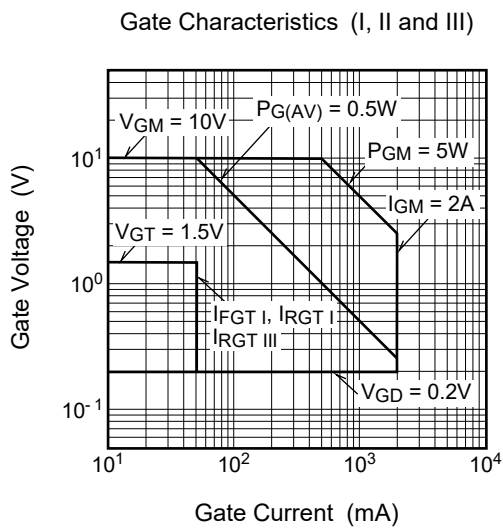
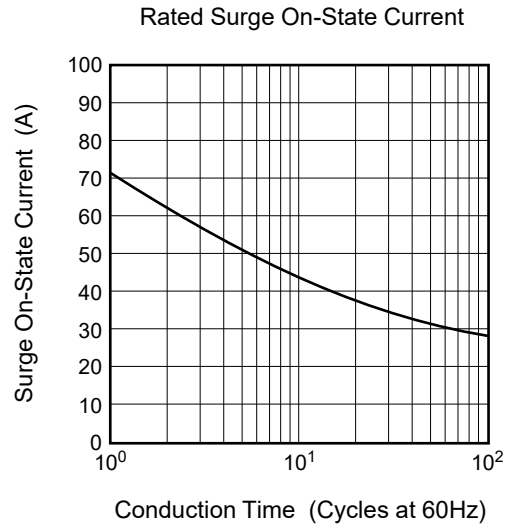
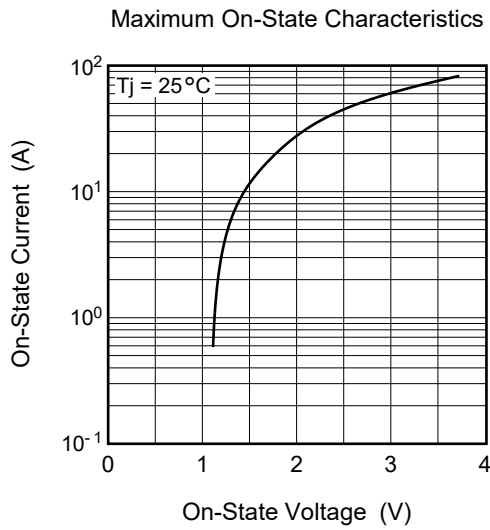
4. Test conditions of the critical-rate of rise of off-state commutation voltage is shown in the table below.

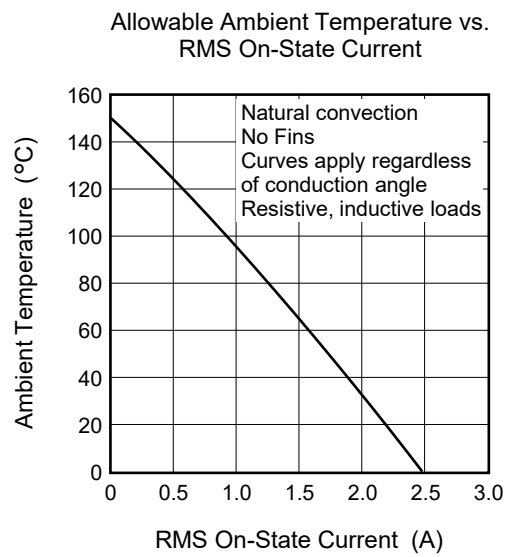
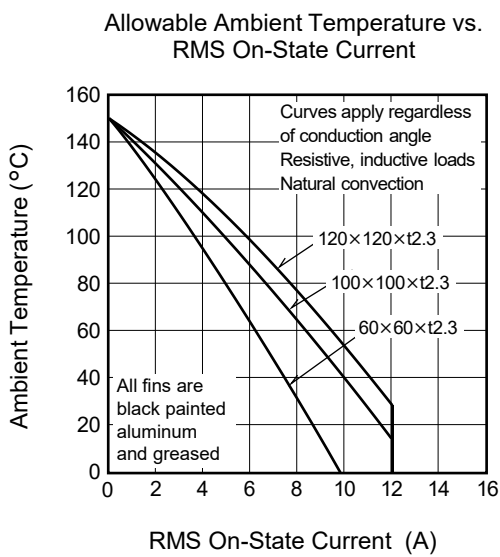
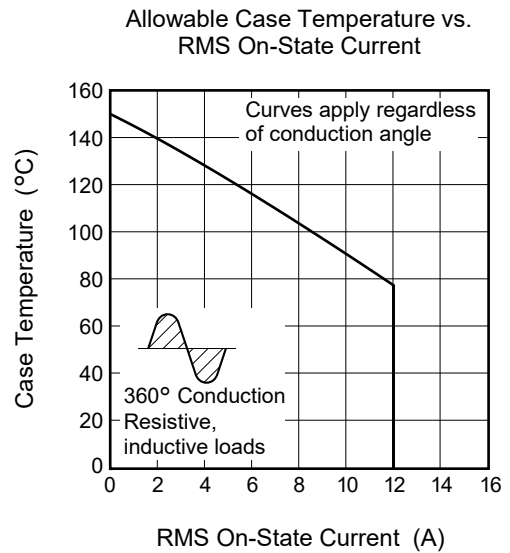
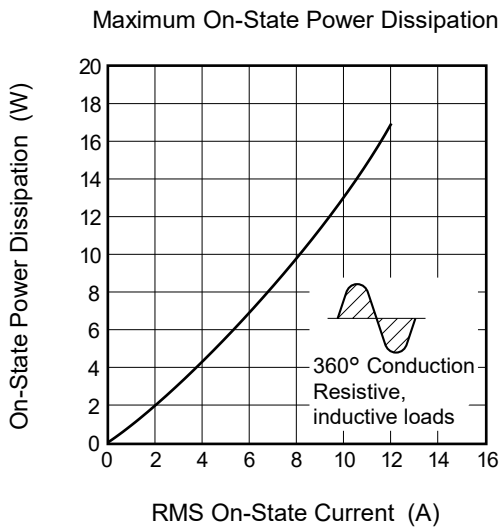
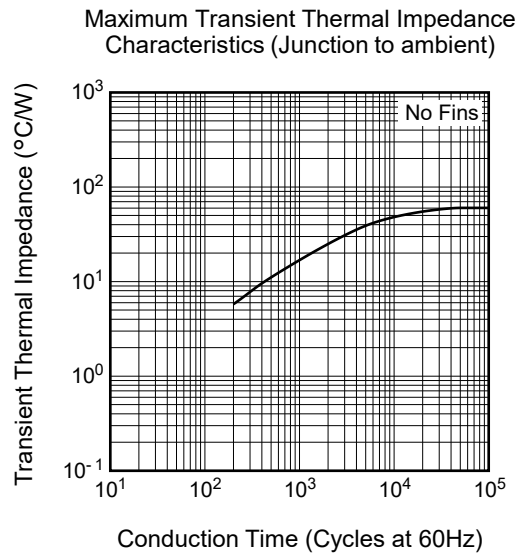
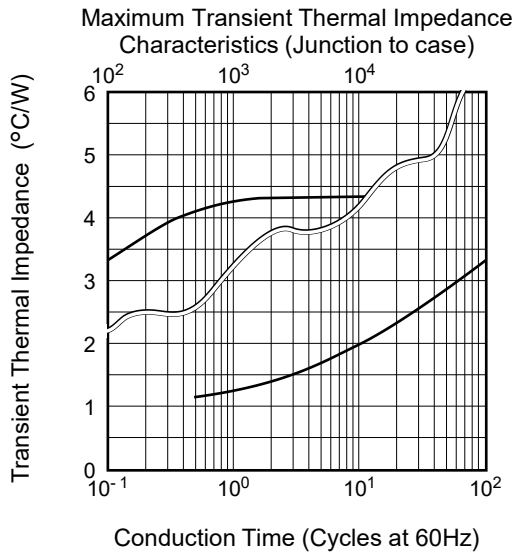
5. Make sure that your finished product containing this device meets your safe isolation requirements.

For safety, it's advisable that heatsink is electrically floating.

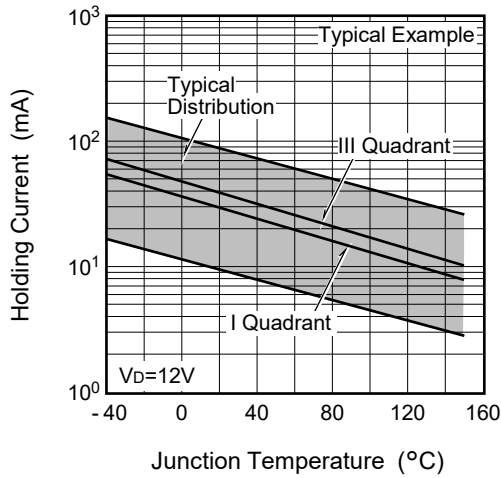
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125^\circ\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c = -6\text{ A/ms}$ 3. Peak off-state voltage $V_D = 400\text{ V}$	

Performance Curves

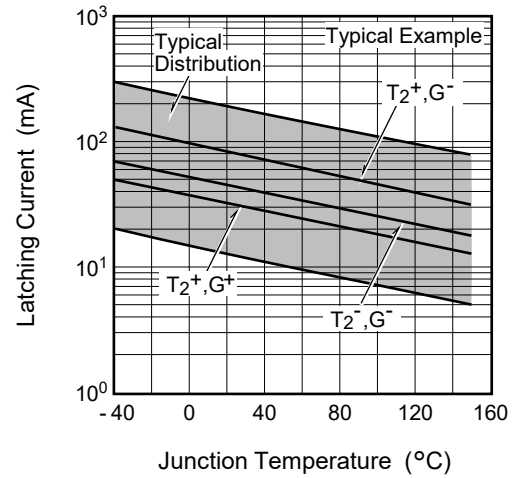




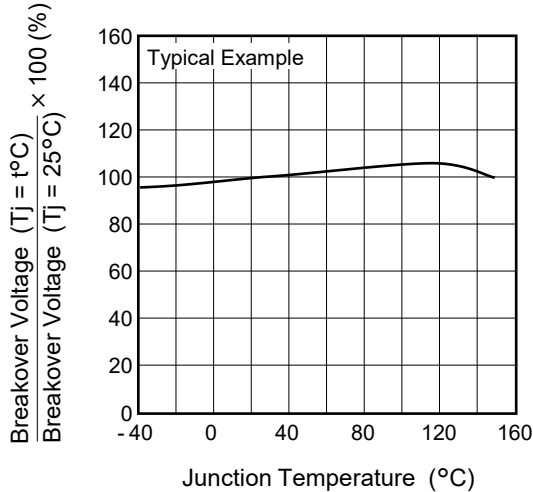
Holding Current vs. Junction Temperature



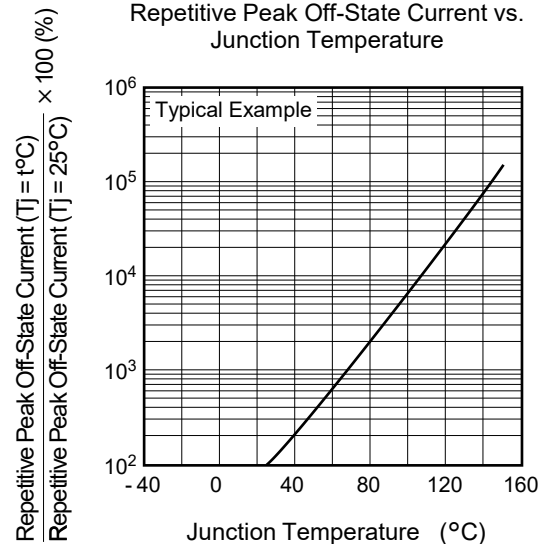
Latching Current vs. Junction Temperature



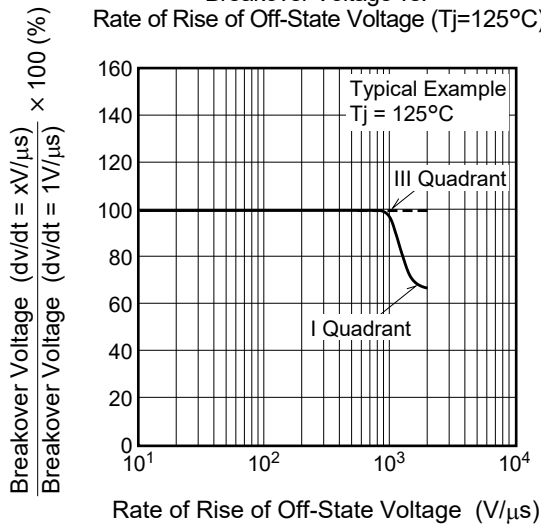
Breakover Voltage vs. Junction Temperature



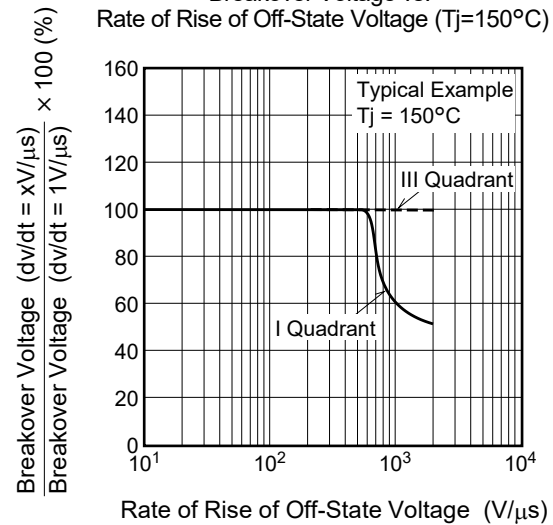
Repetitive Peak Off-State Current vs. Junction Temperature



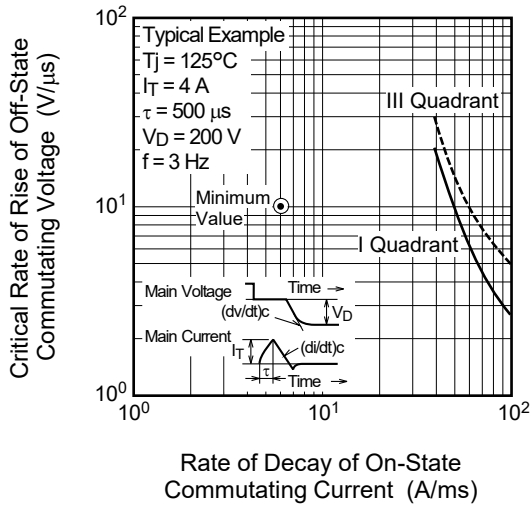
Breakover Voltage vs. Rate of Rise of Off-State Voltage (T<sub>J</sub>=125°C)



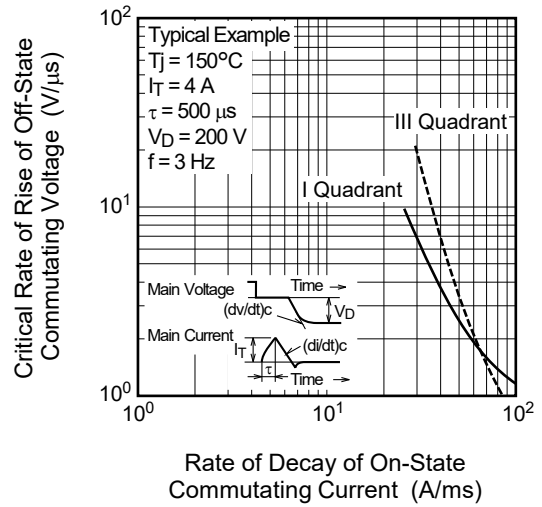
Breakover Voltage vs. Rate of Rise of Off-State Voltage (T<sub>J</sub>=150°C)



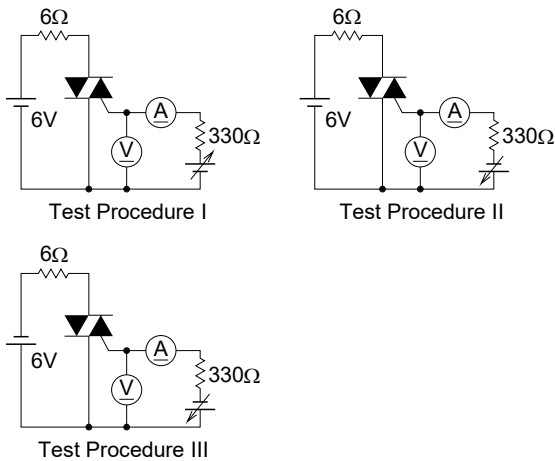
Commutation Characteristics (Tj=125°C)



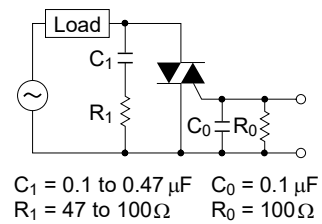
Commutation Characteristics (Tj=150°C)



Gate Trigger Characteristics Test Circuits



Recommended peripheral components for Triac

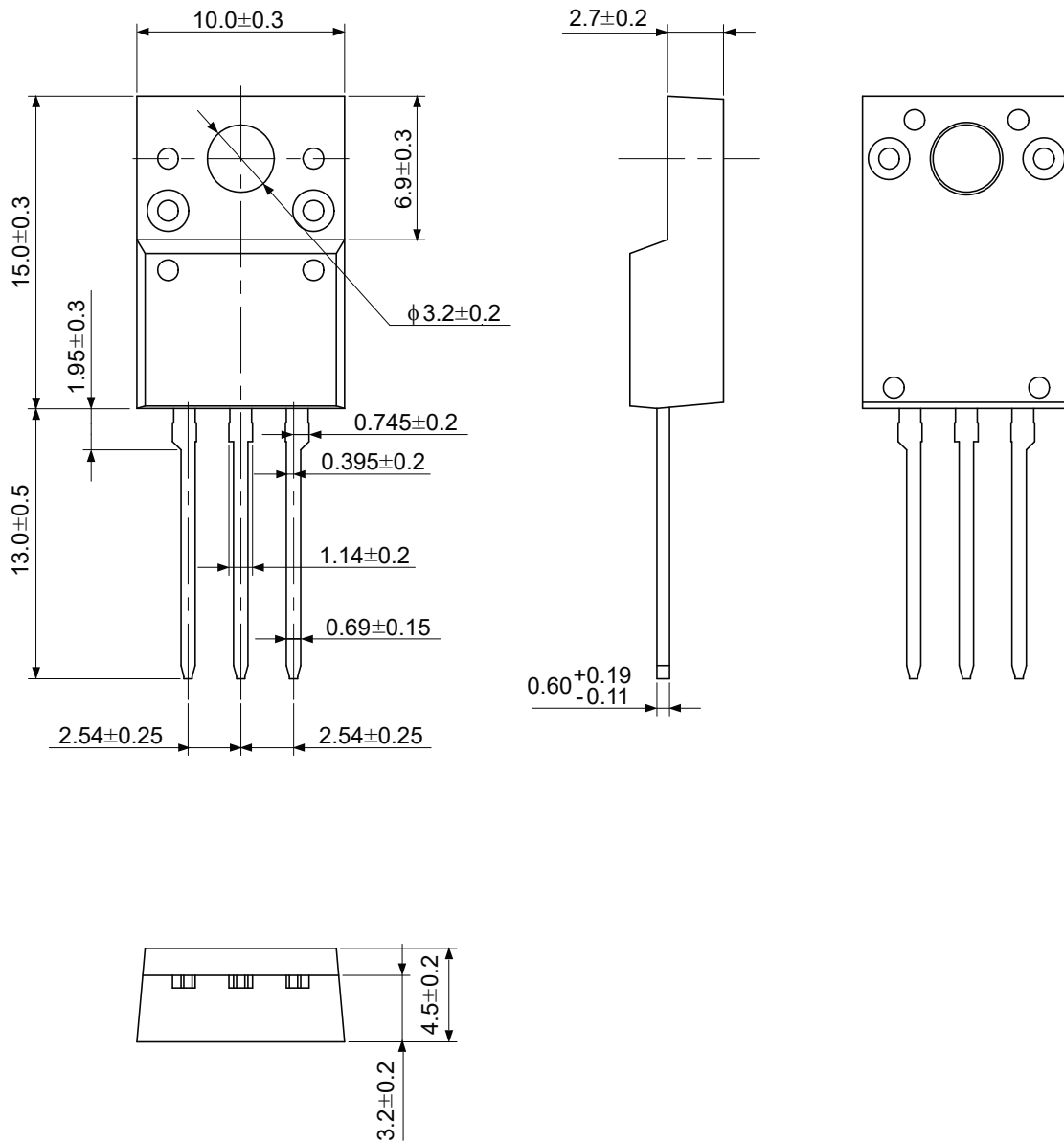


### Package Dimensions

Ordering code: #BG0

JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
-	PRSS0003AP-A	TO-220FPA	1.65

Unit: mm







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